











CSD19505KCS

SLPS480B - JANUARY 2014-REVISED OCTOBER 2014

CSD19505KCS 80 V N-Channel NexFET™ Power MOSFET

Features

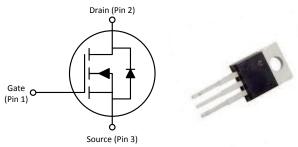
- Ultra-Low Qa and Qad
- Low Thermal Resistance
- Avalanche Rated
- Pb-Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- TO-220 Plastic Package

Applications

- Secondary Side Synchronous Rectifier
- Motor Control

Description

This 80 V, 2.6 m Ω , TO-220 NexFETTM power MOSFET is designed to minimize losses in power conversion applications.



Product Summary

$T_A = 25^\circ$	С	TYPICAL VA	UNIT		
V_{DS}	Drain-to-Source Voltage 80				
Q_g	Gate Charge Total (10 V)	76	nC		
Q _{gd}	Gate Charge Gate to Drain	11	nC		
D	Drain to Course On Desistance	V _{GS} = 6 V	2.9	mΩ	
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 10 V	2.6	mΩ	
V _{GS(th)}	Threshold Voltage 2.6				

Ordering Information⁽¹⁾

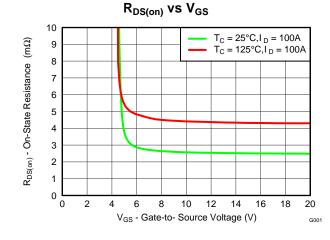
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Device	Package	Media	Qty	Ship
CSD19505KCS	TO-220 Plastic Package	Tube	50	Tube

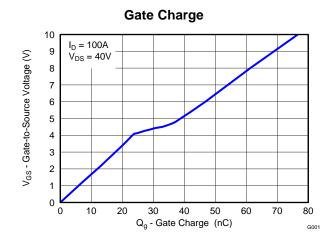
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	±20	V
	Continuous Drain Current (Package limited)	150	
I _D	Continuous Drain Current (Silicon limited), T _C = 25°C	208	Α
	Continuous Drain Current (Silicon limited), T _C = 100°C	147	
I_{DM}	Pulsed Drain Current (1)	400	Α
P_D	Power Dissipation	300	W
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 175	°C
E _{AS}	Avalanche Energy, single pulse I _D = 101 A, L = 0.1 mH, R _G = 25 Ω	510	mJ

(1) Max $R_{\theta JC} = 0.5^{\circ}C/W$, pulse duration $\leq 100~\mu s$, duty cycle $\leq 1\%$







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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (February 2014) to Revision B	Page
 Updated Pulsed Drain Current Conditions Updated the SOA in Figure 10 	
Changes from Original (January 2014) to Revision A	Page
Increased Pulsed Drain Current Limit	4
	1

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5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN T	YP MA	X UNIT
STATIC	CHARACTERISTICS				
BV _{DSS}	Drain-to-Source Voltage	V _{GS} = 0 V, I _D = 250 μA	80		V
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 64 V			1 μA
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = 20 V		10	00 nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.2	2.6 3	.2 V
D	Drain-to-Source On-Resistance	$V_{GS} = 6 \text{ V}, I_D = 100 \text{ A}$		2.9 3	.8 mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 100 \text{ A}$		2.6 3	.1 mΩ
9 _{fs}	Transconductance	V _{DS} = 8 V, I _D = 100 A	2	262	S
DYNAMI	C CHARACTERISTICS				
C _{iss}	Input Capacitance		60	90 782	:0 pF
C _{oss}	Output Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 40 \text{ V}, f = 1 \text{ MHz}$	16	600 208	0 pF
C _{rss}	Reverse Transfer Capacitance			26 3	4 pF
R_G	Series Gate Resistance			1.4 2	.8 Ω
Q_g	Gate Charge Total (10 V)			76	nC
Q _{gd}	Gate Charge Gate to Drain	V 40 V I 400 A		11	nC
Q_{gs}	Gate Charge Gate to Source	V _{DS} = 40 V, I _D = 100 A		25	nC
Q _{g(th)}	Gate Charge at V _{th}			15	nC
Q _{oss}	Output Charge	V _{DS} = 40 V, V _{GS} = 0 V	2	214	nC
t _{d(on)}	Turn On Delay Time			31	ns
t _r	Rise Time	V _{DS} = 50 V, V _{GS} = 10 V,		16	ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 100 \text{ A}, R_G = 0 \Omega$		62	ns
t _f	Fall Time			6	ns
DIODE C	CHARACTERISTICS				· — — —
V _{SD}	Diode Forward Voltage	I _{SD} = 100 A, V _{GS} = 0 V		0.9 1	.1 V
Q _{rr}	Reverse Recovery Charge	V _{DS} = 40 V, I _F = 100 A,	4	100	nC
t _{rr}	Reverse Recovery Time	di/dt = 300 A/µs		88	ns

5.2 Thermal Information

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

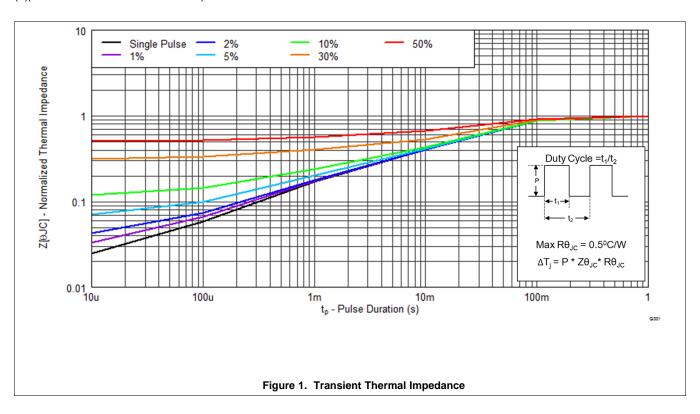
	THERMAL METRIC	MIN	TYP	MAX	UNIT
R_{\thetaJC}	Junction-to-Case Thermal Resistance			0.5	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			62	C/VV

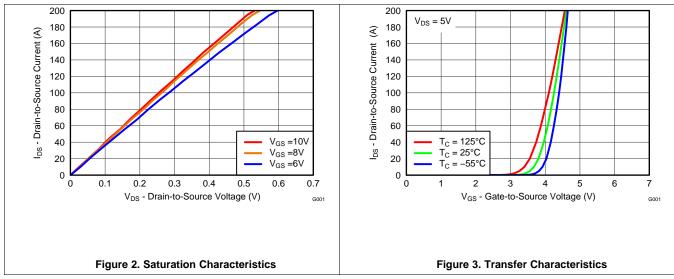
Product Folder Links: CSD19505KCS



5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

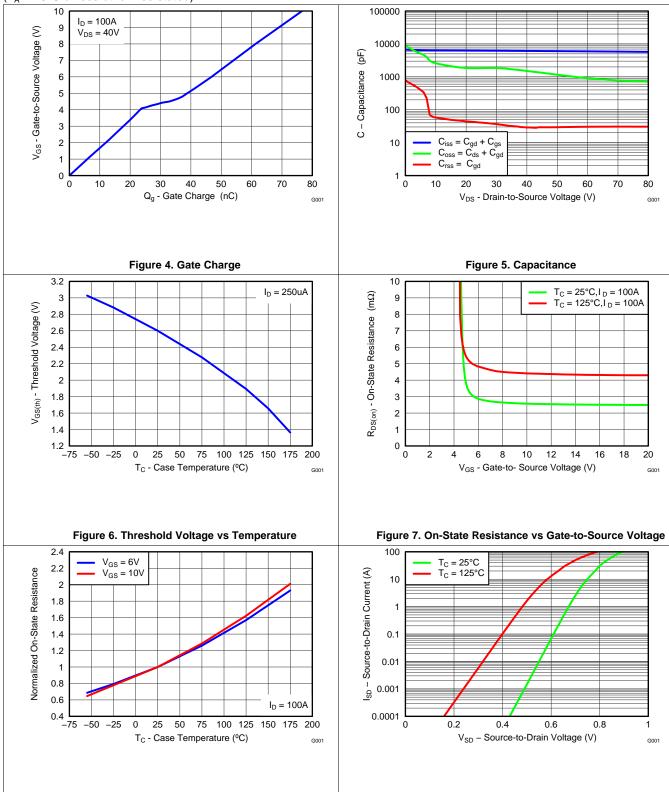






Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)



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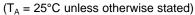
Figure 8. Normalized On-State Resistance vs Temperature

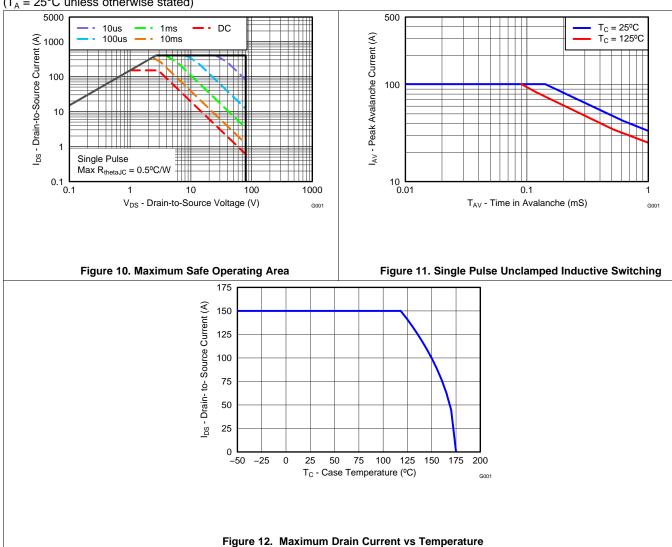
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Figure 9. Typical Diode Forward Voltage



Typical MOSFET Characteristics (continued)







6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

Product Folder Links: CSD19505KCS



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

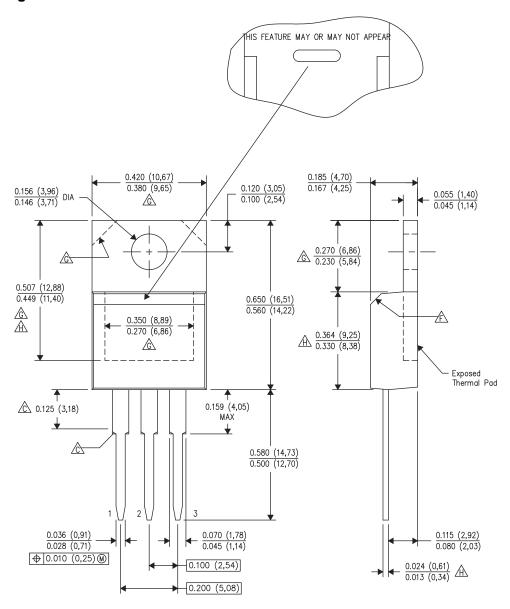
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7.1 KCS Package Dimensions



NOTES: All linear dimensions are in inches (millimeters).

This drawing is subject to change without notice.

Lead dimensions are not controlled within this area. Chamfer may or may not appear D. All lead dimensions apply before solder dip. E. The center lead is in electrical contact with the mounting tab.

The center lead is in electrical contact with the mounting tab.

The chamfer is optional.

Thermal pad contour optional within these dimensions.

⚠ Falls within JEDEC TO-220 variation AB, except minimum lead thickness, minimum exposed pad length, and maximum body length.

Pin Configuration

Position	Designation
Pin 1	Gate
Pin 2 / Tab	Drain
Pin 3	Source

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PACKAGE OPTION ADDENDUM

18-Oct-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CSD19505KCS	ACTIVE	TO-220	KCS	3	50	Pb-Free (RoHS)	CU SN	N / A for Pkg Type	-55 to 175	CSD19505KCS	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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18-Oct-2014

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